

Title (en)

SILICON ON INSULATOR LOGIC CIRCUIT UTILIZING DIODE SWITCHING ELEMENTS

Title (de)

DIODENSCHALTELEMENTE VERWENDENDER SILIZIUM-AUF-ISOLATOR LOGIKSCHALTkreis

Title (fr)

CIRCUIT LOGIQUE A SILICIUM SUR ISOLANT UTILISANT DES ELEMENTS DE COMMUTATION A DIODE

Publication

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Application

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Abstract (en)

[origin: WO0197289A1] A logic circuit is formed on a silicon on insulator (SOI) substrate in the thin silicon layer above the insulating buried oxide layer. The logic circuit both SOI field effect transistors (FETs) and SOI diodes to provide for reduced size of the logic circuit and reduced power consumption when the logic circuit is in operation. A method of performing certain logic function is also provided.

IPC 1-7

H01L 27/12; H03K 19/08; H03K 19/096; H03K 19/12

IPC 8 full level

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CPC (source: EP)

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